

2SK1228

Silicon N-Channel MOS FET

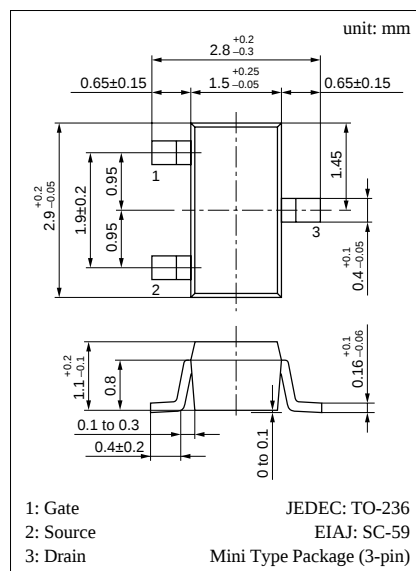
For switching

■ Features

- High-speed switching
- Wide frequency band
- Incorporating a built-in gate protection-diode
- Allowing 2.5V drive

■ Absolute Maximum Ratings (Ta = 25°C)

Parameter	Symbol	Ratings	Unit
Drain to Source voltage	V_{DS}	50	V
Gate to Source voltage	V_{GSO}	10	V
Drain current	I_D	50	mA
Max drain current	I_{DP}	100	mA
Allowable power dissipation	P_D	150	mW
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C



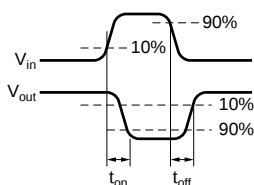
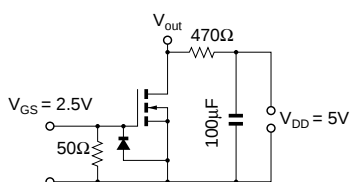
Marking Symbol: 4V

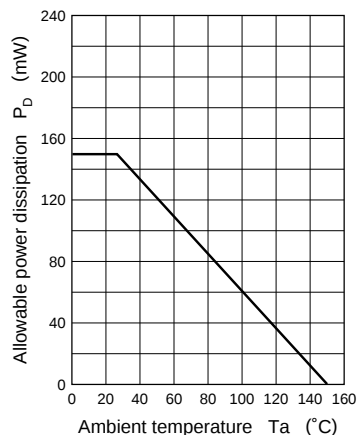
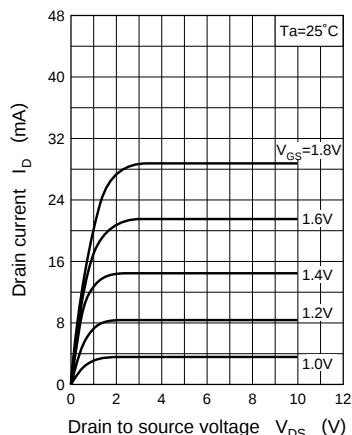
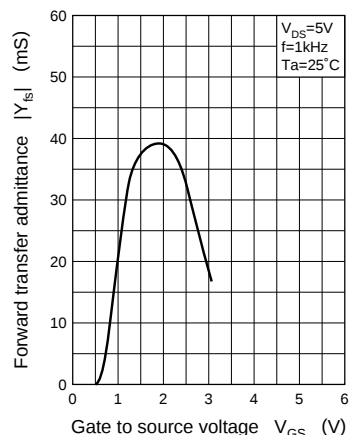
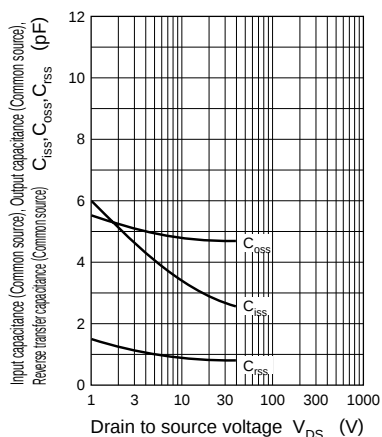
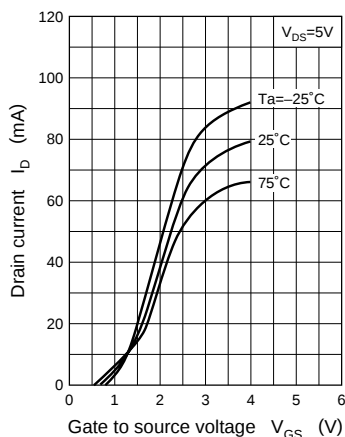
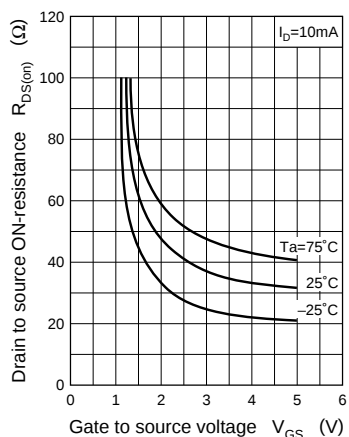
■ Electrical Characteristics (Ta = 25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source cut-off current	I_{DSS}	$V_{DS} = 20V, V_{GS} = 0$			1	μA
Gate to Source leakage current	I_{GSS}	$V_{GS} = 10V, V_{DS} = 0$			1	μA
Drain to Source breakdown voltage	V_{DSS}	$I_D = 10\mu A, V_{GS} = 0$	50	100		V
Gate threshold voltage	V_{th}	$I_D = 100\mu A, V_{DS} = 5V$	0.5	0.8	1.1	V
Drain to Source ON-resistance	$R_{DS(on)}$ ^{*1}	$I_D = 10mA, V_{GS} = 2.5V$		27	50	Ω
Forward transfer admittance	$ Y_{fs} $	$I_D = 10mA, V_{DS} = 5V, f = 1kHz$	20	39		mS
Input capacitance (Common Source)	C_{iss}	$V_{DS} = 5V, V_{GS} = 0, f = 1MHz$		4.5		pF
Output capacitance (Common Source)	C_{oss}			4.1		pF
Reverse transfer capacitance (Common Source)	C_{rss}			1.2		pF
Turn-on time	t_{on} ^{*2}	$V_{DD} = 5V, V_{GS} = 0 \text{ to } 2.5V, R_L = 470\Omega$		0.2		μs
Turn-off time	t_{off} ^{*2}	$V_{DD} = 5V, V_{GS} = 2.5 \text{ to } 0V, R_L = 470\Omega$		0.2		μs

^{*1} Pulse measurement

^{*2} t_{on}, t_{off} measurement circuit



$P_D - T_a$  $I_D - V_{DS}$  $|Y_{fs}| - V_{GS}$  $C_{iss}, C_{oss}, C_{rss} - V_{DS}$  $I_D - V_{GS}$  $R_{DS(on)} - V_{GS}$  $V_{IN} - I_O$ 